

TRANSISTOR (PNP)

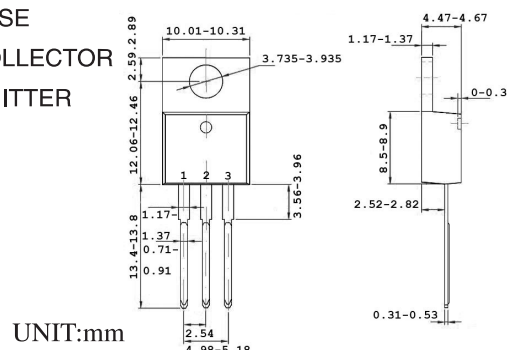
Plastic-Encapsulate Transistor

FEATURES

- High current switching applications
- Low collector saturation voltage:
 $V_{CE(SAT)} = -0.4V(max.)$ at $I_C = -3A$
- High speed switching time:
 $t_{stg} = 1.0\mu s(typ.)$
- Complementary to 2SC2562

TO-220

- BASE
- COLLECTOR
- EMITTER



UNIT:mm

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

MAXIMUM RATINGS

Parameters	Symbols	Value	UNITS
Collector-Base Voltage	V_{CBO}	-60	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current - Continuous	I_C	-5	A
Collector Power Dissipation	P_C	25	W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{stg}	-55-150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

ELECTRICAL CHARACTERISTICS

Parameters	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -1mA, I_E = 0$	-60			V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-50			V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-5			V
Collector Cut-Off Current	I_{CBO}	$V_{CB} = -50V, I_E = 0$			-1	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-1	μA
DC Current Gain	$h_{FE(1)}$ $h_{FE(2)}$ *	$V_{CE} = -1V, I_C = -1A$ $V_{CE} = -1V, I_C = 3A$	70 30		240	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$ *	$I_C = -3A, I_B = 150mA$		-0.2	-0.4	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -3A, I_B = 150mA$		-0.9	-1.2	V
Transition Frequency	f_T	$V_{CE} = -4V, I_C = -1A$		60		MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		170		pF
Switching Time	Turn-on Time	t_{on}		0.1		μs
	Storage Time	t_{stg}		1.0		
	Fall Time	t_f		0.1		

Note: $h_{FE(1)}$ Classification O:70-140, Y:120-240

*Pulse test: $t_p \leq 300\mu s; \delta \leq 0.02$.